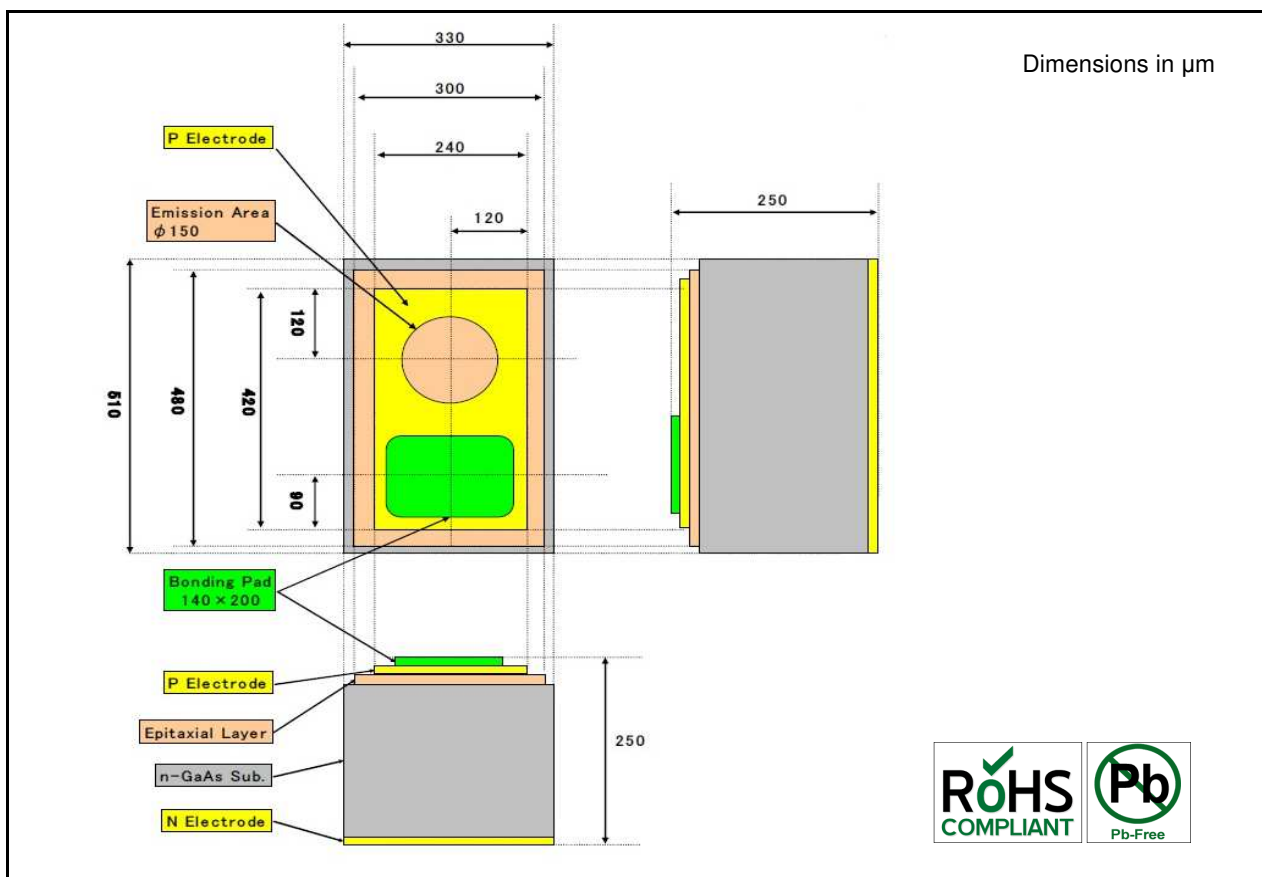


LED Chip Infrared

EOLC-850-19-15

Rev. 04, 2017

Radiation	Type	Electrodes
Infrared	AlGaAs	P (anode) up



Absolute Maximum Ratings

T_{amb}= 25°C, unless otherwise specified

Parameter	Symbol	Rating	Unit
Forward current	I _F	80	mA
Reverse voltage	V _R	5	V
Junction temperature	T _J	100	°C

Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F =20 mA	V _F		1.45	1.8	V
Reverse current	V _R =5 V	I _R			10	μA
Radiant power	I _F =20 mA	Φ _e	1	1.5	2	mW
Peak wavelength	I _F =20 mA	λ _p	830	850	870	nm

Art. No. 114 012

We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.